

BAT41

V_{RRM} : 100V

FEATURES :

- For general purpose applications
- This diode features low turn-on voltage and high breakdown voltage. This device is protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges
- This diode is also available in a MiniMELF case with type designation LL41
- Pb / RoHS Free

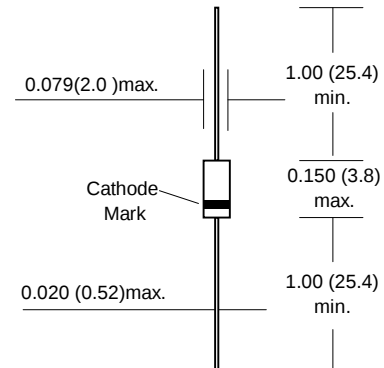
MECHANICAL DATA :

Case: DO-35 Glass Case

Weight: approx. 0.13g

SCHOTTKY BARRIER DIODE

**DO - 35 Glass
(DO-204AH)**



Dimensions in inches and (millimeters)

Maximum Ratings and Thermal Characteristics (Rating at 25 °C ambient temperature unless otherwise specified.)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	100	V
Continuous Forward Current	I_F	100 ⁽¹⁾	mA
Repetitive Peak Forward Current at $t_p < 1s$	I_{FRM}	350 ⁽¹⁾	mA
Forward Surge Current at $t_p = 10 ms$,	I_{FSM}	750 ⁽¹⁾	mA
Power Dissipation	P_D	400 ⁽¹⁾	W
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	300 ⁽¹⁾	°C/W
Junction Temperature	T_J	125	°C
Ambient Operating Temperature Range	T_a	-65 to + 125	°C
Storage temperature range	T_S	-65 to + 150	°C

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Breakdown Voltage ⁽²⁾	$V_{(BR)R}$	$I_R = 100 \mu\text{A}$	100	110	-	V
Reverse Current ⁽²⁾	I_R	$V_R = 50 \text{ V}$ $V_R = 50 \text{ V}, T_J = 100^\circ\text{C}$	-	-	100 20	nA μA
Forward Voltage Drop ⁽²⁾	V_F	$I_F = 1\text{mA}$ $I_F = 200\text{mA}$	-	0.4 -	0.45 1.0	V
Diode Capacitance	C_d	$V_R = 0 \text{ V}, f = 1\text{MHz}$	-	2	-	pF
Reverse Recovery Time	T_{rr}	$I_F = 10\text{mA}, I_R = 10\text{mA},$ $I_{rr} = 1\text{mA}, R_L = 100\Omega$	-	5	-	ns

Note: (1) Valid provided that leads at a distance of 4mm from case are kept at ambient temperature.

(2) Pulse test, $t_p = 300\mu\text{s}$